

TF2103M

Half-Bridge Gate Driver

Features

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- Designed for enhanced performance in noisy motor applications
- 290mA source/600mA sink output current capability
- Outputs tolerant to negative transients
- Internal dead time of 420ns to protect MOSFETs
- Wide low side gate driver supply voltage: 10V to 20V
- Logic input (HIN and LIN*) 3.3V capability
- Schmitt triggered logic inputs
- Undervoltage lockout for V_{cc} (logic and low side supply)
- Extended temperature range: -40°C to +125°C

Description

The TF2103M is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. TF Semiconductors's high voltage process enables the TF2103M high side to switch to 600V in a bootstrap operation.

The TF2103M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. TF2103M has a fixed internal deadtime of 420ns (typical).

The TF2103M is offered in a SOIC-8(N) and PDIP-8 package and operates over an extended -40 °C to +125 °C temperature range.

Applications

- Motor Controls
- DC-DC Converters
- AC-DC Inverters
- Motor Drives

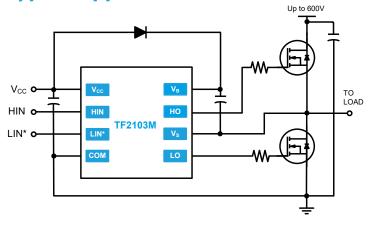




SOIC-8(N)

PDIP-8

Typical Application



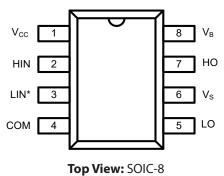
Ordering Information

Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF2103M-3AS	PDIP-8	Tube / 50	YYWW ▼▼TF2103M Lot ID
TF2103M-TAU	SOIC-8(N)	Tube / 100	YYWW TF2103M
TF2103M-TAH	SOIC-8(N)	T&R / 2500	Lot ID

www.tfsemi.com Rev 1.3



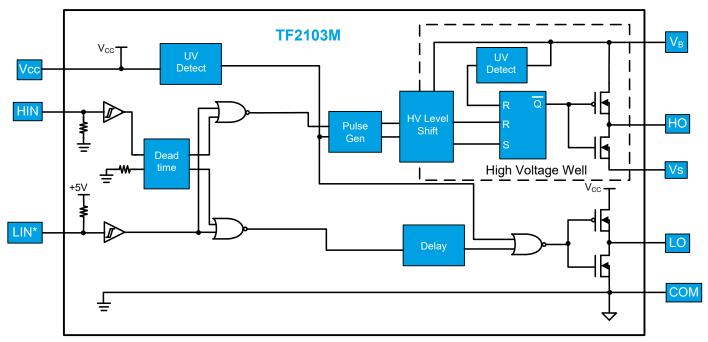


TF2103M

Pin Descriptions

PIN NAME	PIN NUMBER	PIN DESCRIPTION
V _{cc}	1	Logic and low side supply
HIN	2	Logic input for high-side gate driver output in phase with HO
LIN*	3	Logic input for low-side gate driver output out of phase with LO
COM	4	Low-side and logic return
LO	5	Low-side gate drive output
V _s	6	High-side floating supply return
НО	7	High-side gate drive output
V _B	8	High-side floating supply

Functional Block Diagram





Absolute Maximum Ratings (NOTE1)

$V_{\scriptscriptstyle B}$ - High side floating supply voltage0.3V to +624V
V_s - High side floating supply offset voltage V_B -24V to V_B +0.3V
V_{HO} -High side floating output voltage V_s -0.3V to V_B +0.3V
dV_s/dt - Offset supply voltage transient50 V/ns
•
V_{cc} - Low-side fixed supply voltage0.3V to +24V
V_{10}^{cc} - Low-side output voltage0.3V to V_{cc} +0.3V
V_{IN}^{-1} - Logic input voltage (HIN and LIN*)0.3V to V_{CC}^{-1} +0.3V

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

P_D - Package power dissipation at $T_A \le 25$ °C SOIC-8	0.625W
SOIC-8(N) Thermal Resistance (NOTE2) θ_{JA}	200 °C/W
T_J - Junction operating temperature T_L - Lead Temperature (soldering, 10 seconds) T_{stg} - Storage temerature	+300°C

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
V _B	High side floating supply absolute voltage	V _s + 10	V _s + 20	V
V _s	High side floating supply offset voltage	NOTE3	600	V
V _{HO}	High side floating output voltage	V _s	V _B	V
V _{cc}	Low side fixed supply voltage	10	20	V
V _{LO}	Low side output voltage	0	V _{cc}	V
V _{IN}	Logic input voltage (HIN and LIN*)	0	5	V
T _A	Ambient temperature	-40	125	°C

NOTE3 Logic operational for VS of -5V to +600V. Logic state held for VS of -5V to -VBS

Jul 2019



DC Electrical Characteristics (NOTE4)

 $\rm V_{BIAS} \, (V_{CC}, V_{BS} \,) = 15V, T_A = 25 \, ^{\circ} C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V _{IH}	Logic "1" (HIN) & Logic "0" (LIN*) input voltage	- V _{cc} = 10V to 20V	2.5			
V _{IL}	Logic "0" (HIN) & Logic "1" (LIN*) input voltage	NOTE5			0.8	V
V _{OH}	High level output voltage, V _{BIAS} - V _O	$I_0 = 2mA$		0.05	0.2	
V _{OL}	Low level output voltage, V _o	$I_0 = 2mA$		0.02	0.1	
I _{LK}	Offset supply leakage current	VB = VS = 600V			50	
I _{BSQ}	Quiescent V _{BS} supply current	V _{IN} = 0V or 5V		60	100	
I _{ccq}	Quiescent V _{cc} supply current	V _{IN} = 0V or 5V		350	500	μΑ
I _{IN+}	Logic "1" input bias current	HIN = 5V, LIN* = 0V		3	10	
I _{IN-}	Logic "0" input bias current	HIN = 0V, LIN* = 5V			5	
$V_{\text{CCUV+}}$	V _{CC} supply under-voltage positive going threshold		8.0	8.9	9.8	
V _{CCUV} -	V _{CC} supply under-voltage negative going threshold		7.4	8.2	9.0	V
V_{BSUV+}	V _{BS} supply under-voltage positive going threshold		4.5	5.5	6.5	V
V _{BSUV} -	V _{BS} supply under-voltage negative going threshold		4.2	5.2	6.2	V
I _{O+}	Output high short circuit pulsed current	$V_O = 0V$, PW $\leq 10 \mu s$	130	290		
I _{o-}	Output low short circuit pulsed current	$V_0 = 15V, PW \le 10 \ \mu s$	270	600		mA

NOTE4 The V_{IIV} V_{TIV} and I_{IN} parameters are applicable to the two logic input pins: HIN and LIN*. The V_o and I_o parameters are applicable to the respective output pins: H0 and L0 **NOTE5** For optimal operation, it is recommended that the input pulse (to HIN and LIN*) should have an amplitude of 2.5V minimum with a pulse width of 840ns minimum.



AC Electrical Characteristics

 $V_{\text{BIAS}}(V_{\text{CC}},V_{\text{BS}})$ = 15V, C_{L} = 1000pF, and T_{A} = 25 °C , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t _{on}	Turn-on propagation delay	$V_s = 0V$		680	820	
t _{off}	Turn-off propagation delay	V _s = 600V		150	220	
t _{DM}	Delay matching, HS & LS turn-on/turn-off				60	nc
t _r	Turn-on rise time			70	170	ns
t _f	Turn-off fall time	$V_s = 0V$		35	90	
t _{DT}	Deadtime: t _{DT LO-HO} & t _{DT HO-LO}		300	420	650	

LO

Half-Bridge Gate Driver

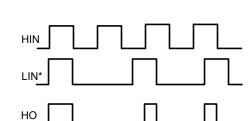


Figure 1. Input / Output Timing Diagram

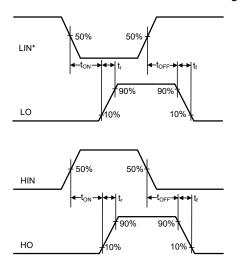


Figure 2. Switching Time Waveform Definitions

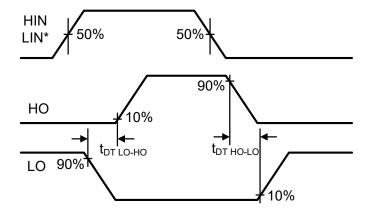
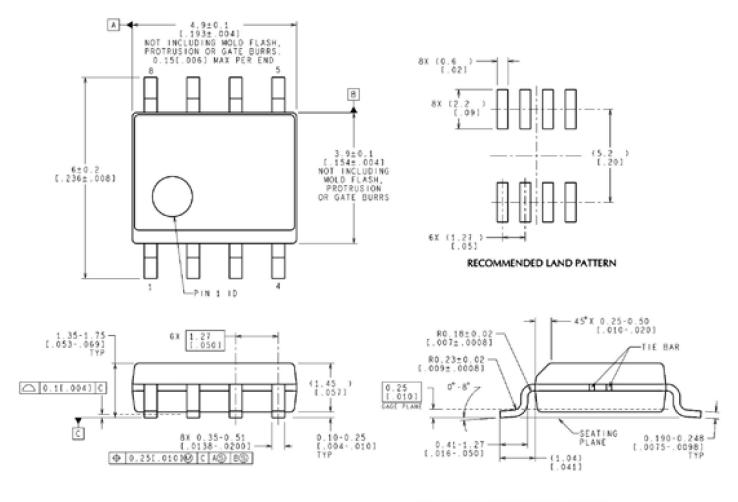


Figure 3. Deadtime Waveform Definitions



Package Dimensions (SOIC-8 N)

Please contact support@telefunkensemi.com for package availability.



NOTES: UNLESS OTHERWISE SPECIFIED

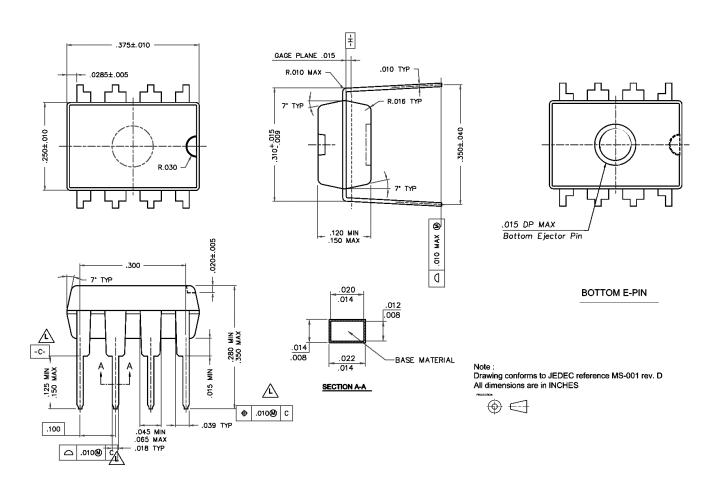
1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.

CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [] ARE INCHES
DIMENSIONS IN () FOR REFERENCE ONLY



Package Dimensions (PDIP-8)

Please contact support@tfsemi.com for package availability.





Revision History

Half-Bridge Gate Driver

Rev.	Change	Owner	Date
1.0	First release, AI datasheet	Keith Spaulding	7/15/2016
1.1	UVLO specifications edited to match repeatability data	Keith Spaulding	10/19/2016
1.2	Edit text	Keith Spaulding	10/20/2017
1.3	Add Note 5	Duke Walton	7/25/2019

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